

# MOSFET - SiC Power, Single N-Channel, TO247-4L

## 650 V, 12 mΩ, 142 A

### NVH4L015N065SC1

#### Features

- Typ.  $R_{DS(on)}$  = 12 mΩ @  $V_{GS} = 18$  V  
Typ.  $R_{DS(on)}$  = 15 mΩ @  $V_{GS} = 15$  V
- Ultra Low Gate Charge ( $Q_{G(tot)} = 283$  nC)
- High Speed Switching with Low Capacitance ( $C_{oss} = 430$  pF)
- 100% Avalanche Tested
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

#### Typical Applications

- Automotive On Board Charger
- Automotive DC/DC Converter for EV/HEV
- Automotive Traction Inverter

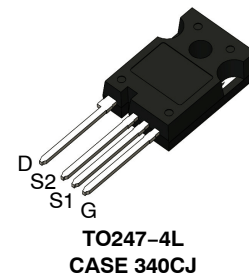
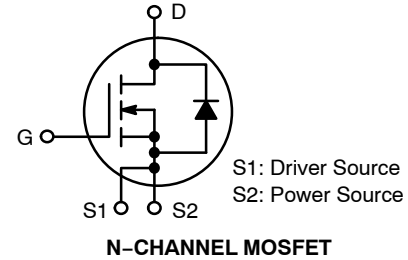
#### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage		$V_{DSS}$	650	V	
Gate-to-Source Voltage		$V_{GS}$	-8/+22	V	
Recommended Operation Values of Gate-to-Source Voltage		$T_C < 175^\circ\text{C}$ $V_{GSop}$	-5/+18	V	
Continuous Drain Current (Note 1)	Steady State	$T_C = 25^\circ\text{C}$	$I_D$	142	A
			$P_D$	500	W
Continuous Drain Current (Note 1)	Steady State	$T_C = 100^\circ\text{C}$	$I_D$	100	A
			$P_D$	250	W
Pulsed Drain Current (Note 2)	$T_C = 25^\circ\text{C}$		$I_{DM}$	483	A
Single Pulse Surge Drain Current Capability	$T_A = 25^\circ\text{C}$ , $t_p = 10 \mu\text{s}$ , $R_G = 4.7 \Omega$	$I_{DSC}$	798	A	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to +175	$^\circ\text{C}$	
Source Current (Body Diode)		$I_S$	114	A	
Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 13$ A, $L = 1$ mH) (Note 3)		$E_{AS}$	84	mJ	
Maximum Lead Temperature for Soldering (1/8" from case for 5 s)		$T_L$	300	$^\circ\text{C}$	

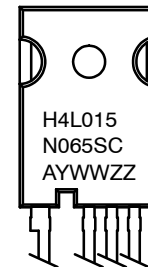
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Repetitive rating, limited by max junction temperature.
3. EAS of 84 mJ is based on starting  $T_J = 25^\circ\text{C}$ ;  $L = 1$  mH,  $I_{AS} = 13$  A,  $V_{DD} = 50$  V,  $V_{GS} = 18$  V.

$V_{(BR)DSS}$	$R_{DS(ON) MAX}$	$I_D MAX$
650 V	18 mΩ @ 18 V	142 A



#### MARKING DIAGRAM



H4L015N065SC = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
ZZ = Lot Traceability

#### ORDERING INFORMATION

Device	Package	Shipping
NVH4L015N065SC1	TO247-4L	30 Units / Tube

# NVH4L015N065SC1

## THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Junction-to-Case - Steady State (Note 1)	$R_{\theta JC}$	0.3	°C/W
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	40	

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	650	-	-	V	
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	$I_D = 20\text{ mA}$ , referenced to $25^\circ\text{C}$	-	0.12	-	V/°C	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}, V_{DS} = 650\text{ V}$	$T_J = 25^\circ\text{C}$	-	-	10	$\mu\text{A}$
			$T_J = 175^\circ\text{C}$	-	-	1	mA
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS} = +18/-5\text{ V}, V_{DS} = 0\text{ V}$	-	-	250	nA	

### ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 25\text{ mA}$	1.8	2.5	4.3	V
Recommended Gate Voltage	$V_{GOP}$		-5	-	+18	V
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = 15\text{ V}, I_D = 75\text{ A}, T_J = 25^\circ\text{C}$	-	15	-	m $\Omega$
		$V_{GS} = 18\text{ V}, I_D = 75\text{ A}, T_J = 25^\circ\text{C}$	-	12	18	
		$V_{GS} = 18\text{ V}, I_D = 75\text{ A}, T_J = 175^\circ\text{C}$	-	16	-	
Forward Transconductance	$g_{FS}$	$V_{DS} = 10\text{ V}, I_D = 75\text{ A}$	-	47	-	S

### CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 325\text{ V}$	-	4790	-	pF
Output Capacitance	$C_{OSS}$		-	430	-	
Reverse Transfer Capacitance	$C_{RSS}$		-	33	-	
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -5/18\text{ V}, V_{DS} = 520\text{ V}, I_D = 75\text{ A}$	-	283	-	nC
Gate-to-Source Charge	$Q_{GS}$		-	72	-	
Gate-to-Drain Charge	$Q_{GD}$		-	64	-	
Gate-Resistance	$R_G$	$f = 1\text{ MHz}$	-	1.6	-	$\Omega$

### SWITCHING CHARACTERISTICS

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -5/18\text{ V}, V_{DS} = 400\text{ V}, I_D = 75\text{ A}, R_G = 2.2\ \Omega$ inductive load	-	23	-	ns
Rise Time	$t_r$		-	26	-	
Turn-Off Delay Time	$t_{d(OFF)}$		-	49	-	
Fall Time	$t_f$		-	9.6	-	
Turn-On Switching Loss	$E_{ON}$		-	167	-	$\mu\text{J}$
Turn-Off Switching Loss	$E_{OFF}$		-	276	-	
Total Switching Loss	$E_{tot}$		-	443	-	

### SOURCE-DRAIN DIODE CHARACTERISTICS

Continuous Source-Drain Diode Forward Current	$I_{SD}$	$V_{GS} = -5\text{ V}, T_J = 25^\circ\text{C}$	-	-	114	A
Pulsed Source-Drain Diode Forward Current (Note 2)	$I_{SDM}$		-	-	483	
Forward Diode Voltage	$V_{SD}$	$V_{GS} = -5\text{ V}, I_{SD} = 75\text{ A}, T_J = 25^\circ\text{C}$	-	4.8	-	V

# NVH4L015N065SC1

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified) (continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>SOURCE-DRAIN DIODE CHARACTERISTICS</b>						
Reverse Recovery Time	$t_{RR}$	$V_{GS} = -5/18\text{ V}$ , $I_{SD} = 75\text{ A}$ , $di_S/dt = 1000\text{ A}/\mu\text{s}$	-	28	-	ns
Reverse Recovery Charge	$Q_{RR}$		-	234	-	nC
Reverse Recovery Energy	$E_{REC}$		-	23	-	$\mu\text{J}$
Peak Reverse Recovery Current	$I_{RRM}$		-	16	-	A
Charge time	$T_a$		-	17	-	ns
Discharge time	$T_b$		-	11	-	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

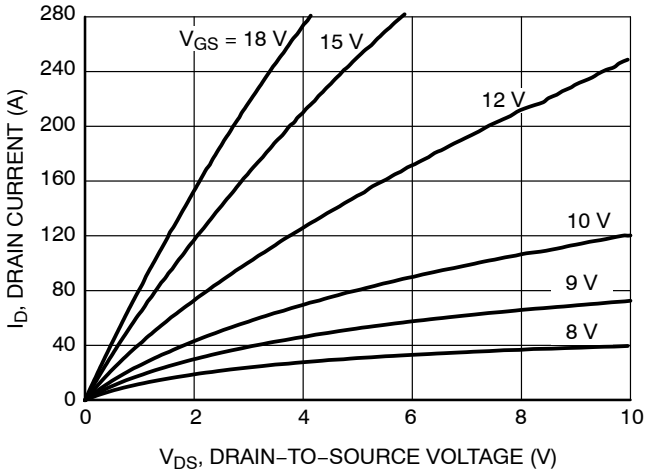


Figure 1. On-Region Characteristics

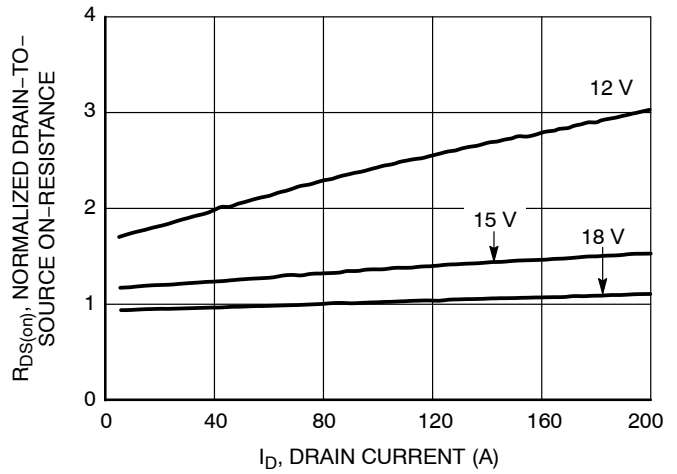


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

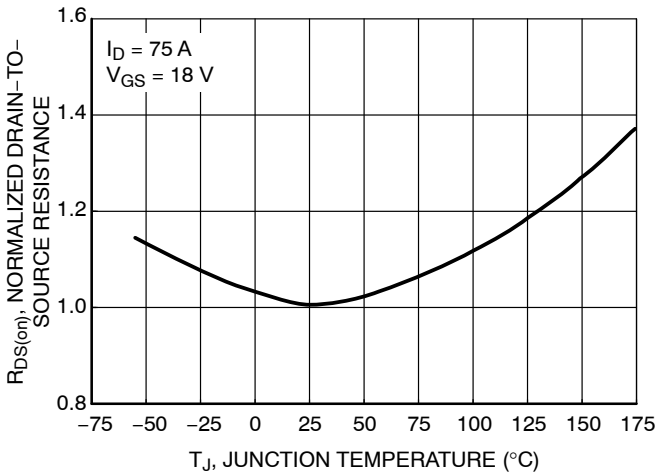


Figure 3. On-Resistance Variation with Temperature

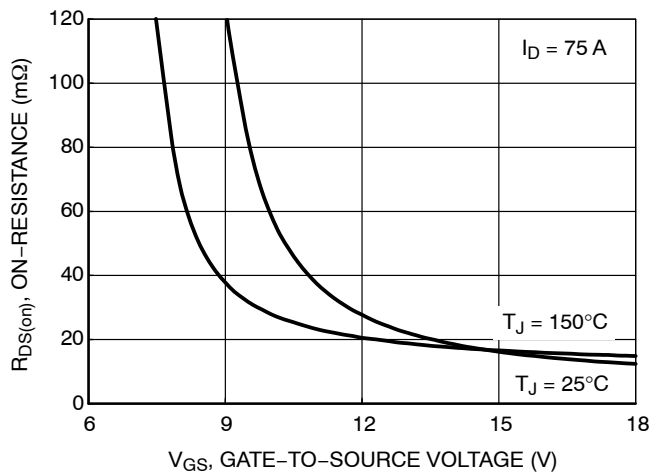


Figure 4. On-Resistance vs. Gate-to-Source Voltage

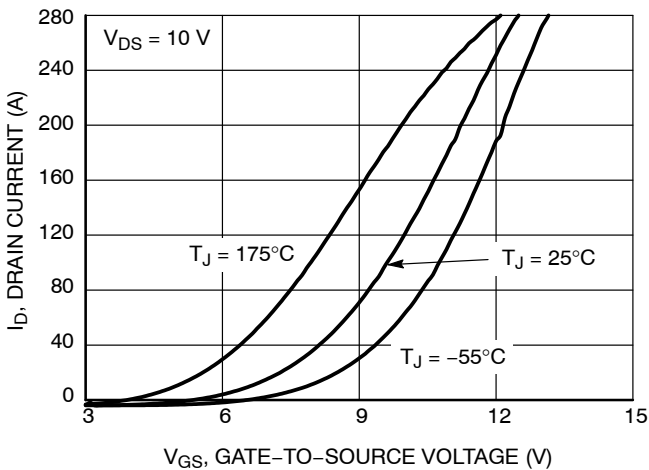


Figure 5. Transfer Characteristics

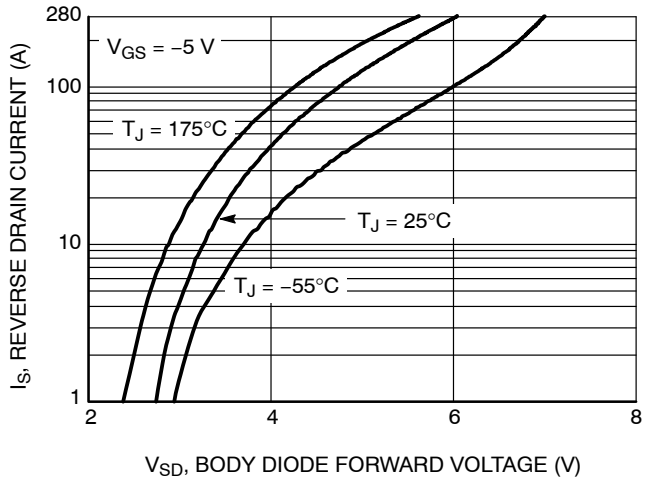
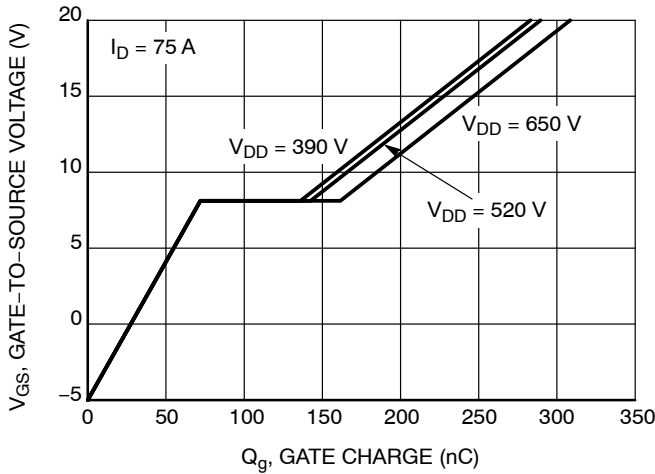


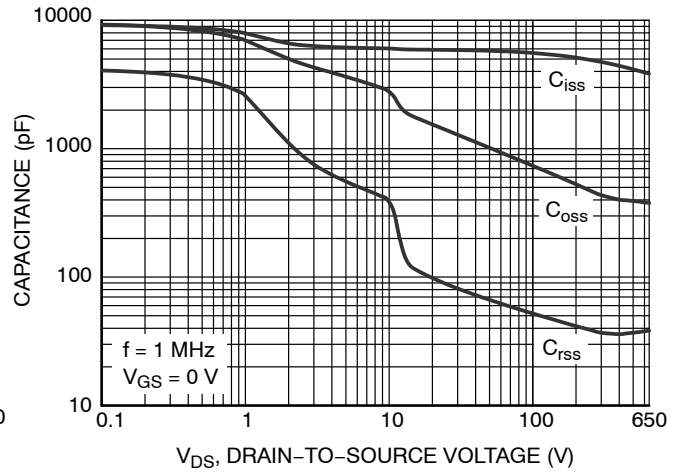
Figure 6. Diode Forward Voltage vs. Current

# NVH4L015N065SC1

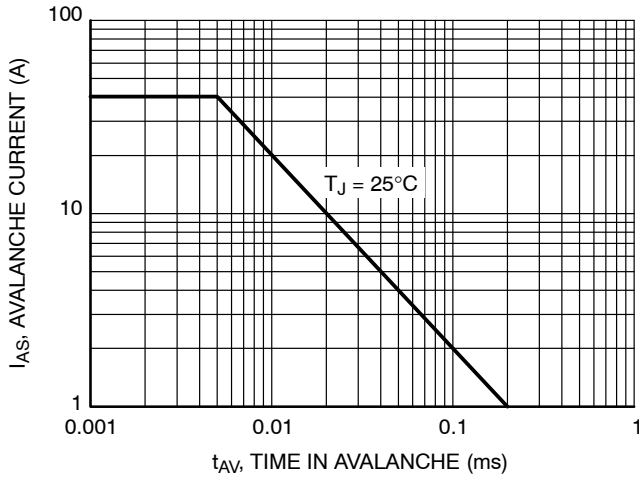
## TYPICAL CHARACTERISTICS



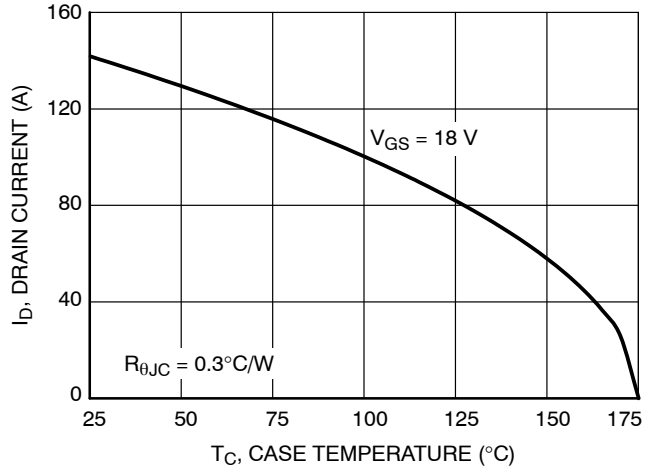
**Figure 7. Gate-to-Source Voltage vs. Total Charge**



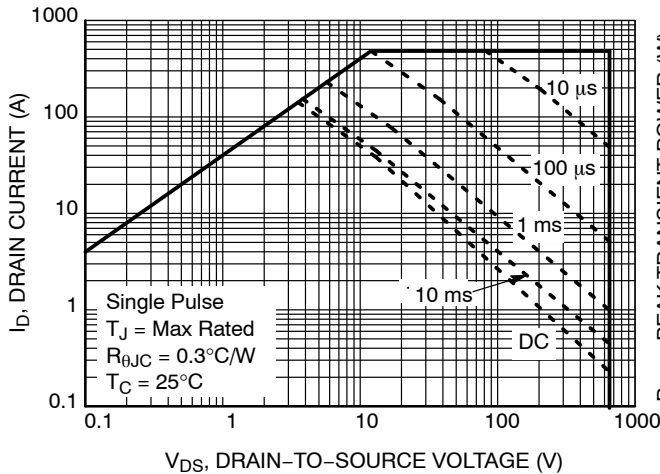
**Figure 8. Capacitance vs. Drain-to-Source Voltage**



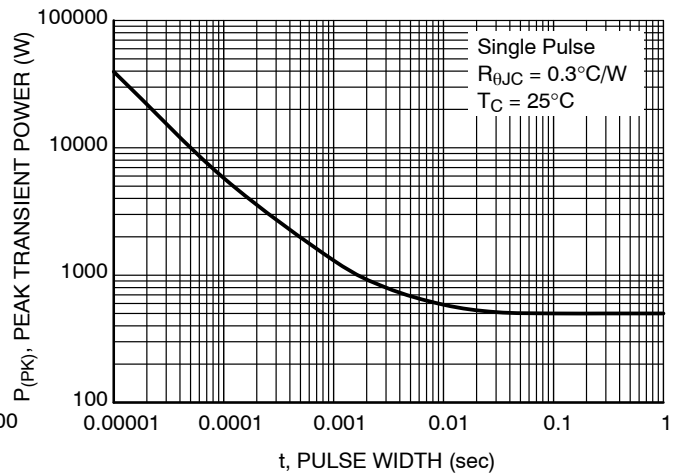
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs. Case Temperature**



**Figure 11. Safe Operating Area**



**Figure 12. Single Pulse Maximum Power Dissipation**

# NVH4L015N065SC1

## TYPICAL CHARACTERISTICS

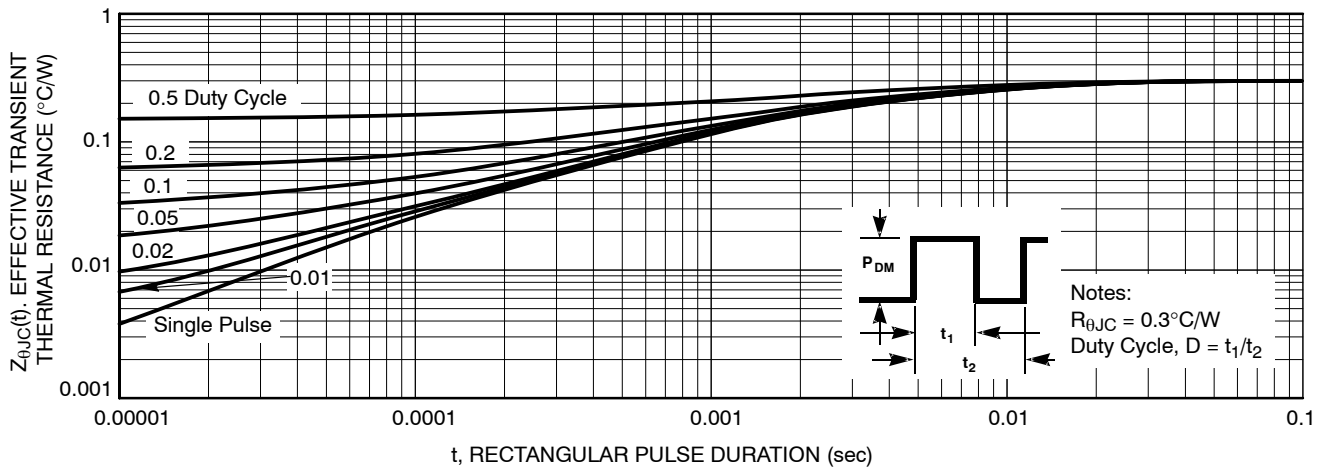


Figure 13. Junction-to-Case Thermal Response

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



TO-247-4LD  
CASE 340CJ  
ISSUE A

DATE 16 SEP 2019



DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.80	5.00	5.20
A1	2.10	2.40	2.70
A2	1.80	2.00	2.20
b	1.07	1.20	1.33
b1	1.20	1.40	1.60
b2	2.02	2.22	2.42
c	0.50	0.60	0.70
D	22.34	22.54	22.74
D1	16.00	16.25	16.50
D2	0.97	1.17	1.37
e	2.54 BSC		
e1	5.08 BSC		
E	15.40	15.60	15.80
E1	12.80	13.00	13.20
E/2	4.80	5.00	5.20
L	18.22	18.42	18.62
L1	2.42	2.62	2.82
p	3.40	3.60	3.80
p1	6.60	6.80	7.00
Q	5.97	6.17	6.37
S	5.97	6.17	6.37

**NOTES:**

- A. NO INDUSTRY STANDARD APPLIES TO THIS PACKAGE.
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5-2009.

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